

Vishay Semiconductors

HEXFRED® Ultrafast Soft Recovery Diode, 200 A



SOT-227

PRODUCT SUMMARY				
V _R	1200 V			
V _F (typical)	2.7 V			
t _{rr} (typical)	150 ns			
I _{F(DC)} at T _C	100 A at 69 °C			

FEATURES

- Fast recovery time characteristic
- · Electrically isolated base plate
- Large creepage distance between terminal
- · Simplified mechanical designs, rapid assembly
- UL approved file E78996
- Compliant to RoHS directive 2002/95/EC
- Designed and qualified for industrial level

DESCRIPTION/APPLICATIONS

The dual diode series configuration (HFA200FA120P) is used for output rectification or freewheeling/clamping operation and high voltage application.

The semiconductor in the SOT-227 package is isolated from the copper base plate, allowing for common heatsinks and compact assemblies to be built.

These modules are intended for general applications such as HV power supplies, electronic welders, motor control and inverters.

ABSOLUTE MAXIMUM RATINGS					
PARAMETER	SYMBOL	TEST CONDITIONS	MAX.	UNITS	
Cathode to anode voltage	V _R		1200	V	
Continuous forward current	I _F	T _C = 69 °C	100		
Single pulse forward current	I _{FSM}	I _{FSM} T _J = 25 °C		Α	
Maximum repetitive forward current	I _{FRM}	Rated V_{R_i} square wave, 20 kHz, T_C = 60 °C	150		
Maximum power dissipation	В	T _C = 25 °C	416	W	
	P _D	T _C = 100 °C	166		
RMS isolation voltage	V _{ISOL}	Any terminal to case, t = 1 minute	2500	V	
Operating junction and storage temperature range	T _J , T _{Stg}		- 55 to + 150	°C	

ELECTRICAL SPECIFICATIONS (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V _{BR}	I _R = 100 μA	1200	-	-	
Forward voltage V _{FM}		I _F = 100 A	-	2.68	3.6	V
	I _F = 200 A	-	3.37	4.7		
		I _F = 100 A, T _J = 150 °C	-	2.7	2.9	
Reverse leakage current I _{RM}	V _R = V _R rated	-	10	75	μA	
	$T_J = 125 ^{\circ}\text{C}, V_R = V_R \text{ rated}$	-	2	-	mA	

HFA200FA120P







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DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Reverse recovery time t _{rr}	+	T _J = 25 °C		-	150	-	
	T _J = 125 °C		-	237	-	ns	
Peak recovery current I _{RRM}	,	T _J = 25 °C	$I_F = 50 \text{ A}$ $dI_F/dt = -200 \text{ A/}\mu\text{s}$ $V_R = 200 \text{ V}$	-	14	-	А
	IRRM	T _J = 125 °C		-	21	-	
Reverse recovery charge	Q_{rr}	T _J = 25 °C		-	1050	-	nC
		T _J = 125 °C		-	2430	-	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Junction to case, single leg conducting	В		-	-	0.3	
Junction to case, both legs conducting	- R _{thJC}		-	-	0.15	°C/W
Case to heatsink	R _{thCS}	Flat, greased and surface	-	0.05	-	
Weight			-	30	-	g
Mounting torque			_	1.3	-	Nm



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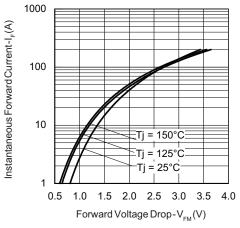


Fig. 1 - Typical Forward Voltage Drop Characteristics

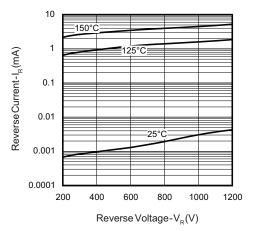


Fig. 2 - Typical Values of Reverse Current vs. Reverse Voltage

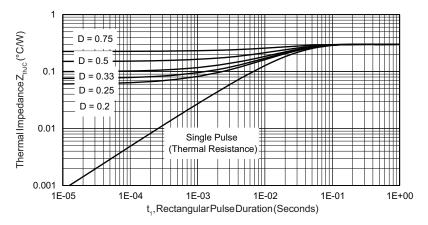


Fig. 3 - Maximum Thermal Impedance Z_{thJC} Characteristics

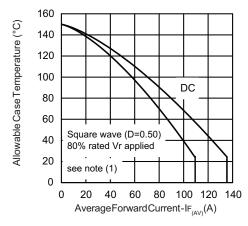


Fig. 4 - Maximum Allowable Case Temperature vs.
Average Forward Current

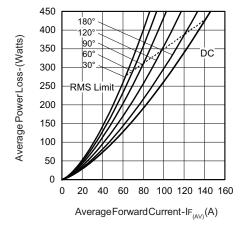


Fig. 5 - Forward Power Loss Characteristics

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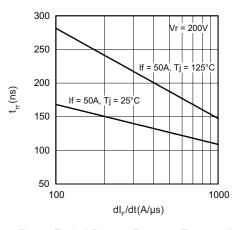


Fig. 6 - Typical Reverse Recovery Time vs. dI_F/dt

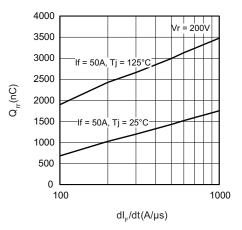


Fig. 7 - Typical Stored Charge vs. dl_F/dt

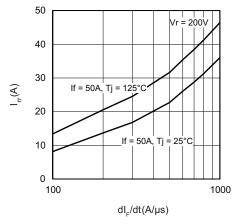


Fig. 8 - Typical Peak Recovery Current vs. dl_F/dt

Note



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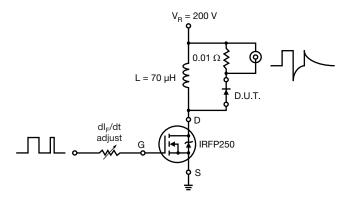
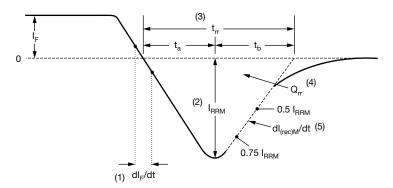


Fig. 9 - Reverse Recovery Parameter Test Circuit



- (1) dl_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) $\rm t_{rr}$ reverse recovery time measured from zero crossing point of negative going $\rm I_{rr}$ to point where a line passing through 0.75 $\rm I_{RRM}$ and 0.50 $\rm I_{RRM}$ extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

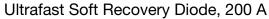
(5) $dl_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 10 - Reverse Recovery Waveform and Definitions

HFA200FA120P

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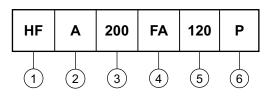
HEXFRED®





ORDERING INFORMATION TABLE

Device code



1 - HEXFRED® family

Process designator (A = Electron irradiated)

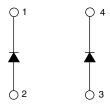
3 - Average current (200 = 200 A)

Package outline (FA = SOT-227)

Voltage rating (120 = 1200 V)

6 - P = Lead (Pb)-free

CIRCUIT CONFIGURATION



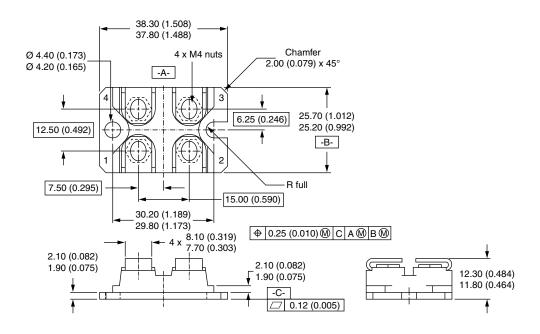
LINKS TO RELATED DOCUMENTS					
Dimensions <u>www.vishay.com/doc?95036</u>					
Packaging information <u>www.vishay.com/doc?95037</u>					



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DIMENSIONS in millimeters (inches)



Notes

- Dimensioning and tolerancing per ANSI Y14.5M-1982
- · Controlling dimension: millimeter

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